

# PATENT ABSTRACTS OF JAPAN

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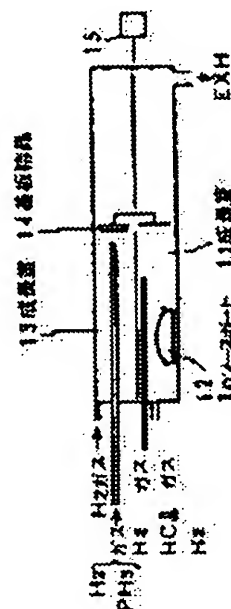
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(21)Application number : 62-165694 (71)Applicant : NEC CORP  
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## (54) METHOD FOR GROWING III-V COMPOUND SEMICONDUCTOR CRYSTAL ON SI SUBSTRATE

### (57)Abstract:

**PURPOSE:** To form the titled semiconductor crystal, having good crystallinity and capable of selective growth on a substrate, by alternately feeding a gas species containing In chloride and a gas species containing a group V constituent element onto a silicon substrate having a formed mask pattern.  
**CONSTITUTION:** An In source boat 12 is placed on the upstream side of a growth chamber 11 in the lower stage and a carrier gas and HCl gas are fed from the upstream side thereof to adsorb the formed In chloride on a silicon substrate 14 having a formed mask pattern. The substrate 14 is then moved to a growth chamber 13 in the upper stage and a gas species containing a group V constituent element is fed and adsorbed on the substrate 14. The above-mentioned operations are alternately repeated to carry out atomic layer epitaxial growth of a III-V compound semiconductor crystal on the substrate 14.



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